

# BAS16XV2

## Switching Diode

### Features

- High-Speed Switching Applications
- Lead Finish: 100% Matte Sn (Tin)
- Qualified Reflow Temperature: 260°C
- Extremely Small SOD-523 Package
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Continuous Reverse Voltage	$V_R$	100	V
Continuous Forward Current	$I_F$	200	mA
Peak Forward Surge Current	$I_{FM(surge)}$	500	mA
Repetitive Peak Forward Current (Pulse Wave = 1 sec, Duty Cycle = 66%)	$I_{FRM}$	500	mA
Non-Repetitive Peak Forward Current (Square Wave, $T_J = 25^\circ\text{C}$ prior to surge)	$I_{FSM}$		A
$t = 1 \mu\text{s}$		4.0	
$t = 1 \text{ ms}$		1.0	
$t = 1 \text{ s}$		0.5	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

### THERMAL CHARACTERISTICS

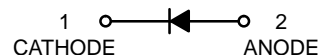
Characteristic	Symbol	Max	Unit
Total Device Dissipation, (Note 1) $T_A = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	200	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	635	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to 150	$^\circ\text{C}$

1. FR-5 Minimum Pad.



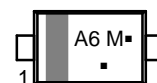
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SOD-523  
CASE 502

### MARKING DIAGRAM



A6 = Specific Device Code  
M = Date Code  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

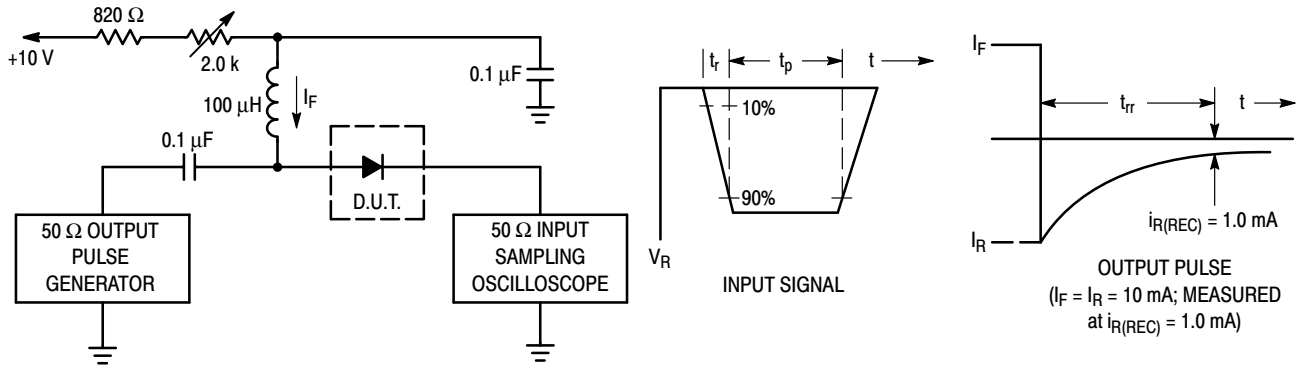
Device	Package	Shipping†
BAS16XV2T1G	SOD-523 (Pb-Free)	3000 / Tape & Reel
BAS16XV2T5G	SOD-523 (Pb-Free)	8000 / Tape & Reel
SBAS16XV2T1G	SOD-523 (Pb-Free)	3000 / Tape & Reel
SBAS16XV2T5G	SOD-523 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# BAS16XV2

## ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>				
Reverse Voltage Leakage Current ( $V_R = 100\text{ V}$ ) ( $V_R = 75\text{ V}, T_J = 150^\circ\text{C}$ ) ( $V_R = 25\text{ V}, T_J = 150^\circ\text{C}$ )	$I_R$	–	1.0 50 30	$\mu\text{A}$
Reverse Breakdown Voltage ( $I_{BR} = 100\ \mu\text{A}$ )	$V_{(BR)}$	100	–	V
Forward Voltage ( $I_F = 1.0\text{ mA}$ ) ( $I_F = 10\text{ mA}$ ) ( $I_F = 50\text{ mA}$ ) ( $I_F = 150\text{ mA}$ )	$V_F$	–	715 855 1000 1250	mV
Diode Capacitance ( $V_R = 0, f = 1.0\text{ MHz}$ )	$C_D$	–	2.0	pF
Forward Recovery Voltage ( $I_F = 10\text{ mA}, t_r = 20\text{ ns}$ )	$V_{FR}$	–	1.75	V
Reverse Recovery Time ( $I_F = I_R = 10\text{ mA}, R_L = 50\ \Omega$ )	$t_{rr}$	–	6.0	ns
Stored Charge ( $I_F = 10\text{ mA}$ to $V_R = 5.0\text{ V}, R_L = 500\ \Omega$ )	$Q_S$	–	45	pC



- Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current ( $I_F$ ) of 10 mA.  
 2. Input pulse is adjusted so  $I_{R(\text{peak})}$  is equal to 10 mA.  
 3.  $t_p \gg t_{rr}$

**Figure 1. Recovery Time Equivalent Test Circuit**

# BAS16XV2

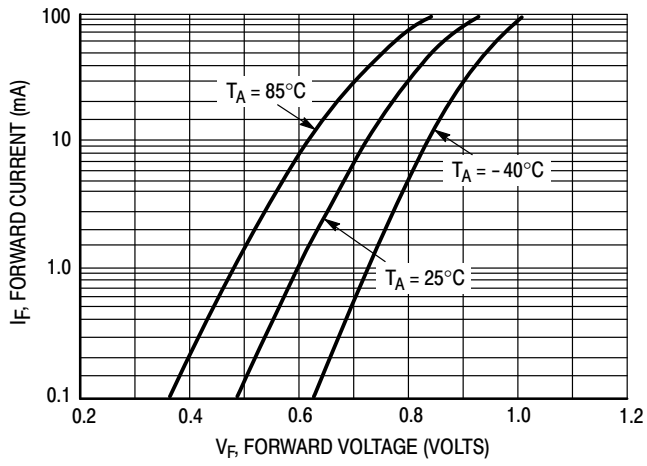


Figure 2. Forward Voltage

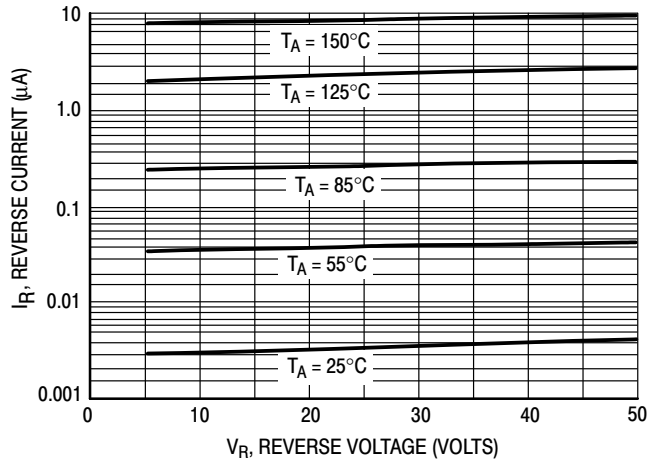


Figure 3. Leakage Current

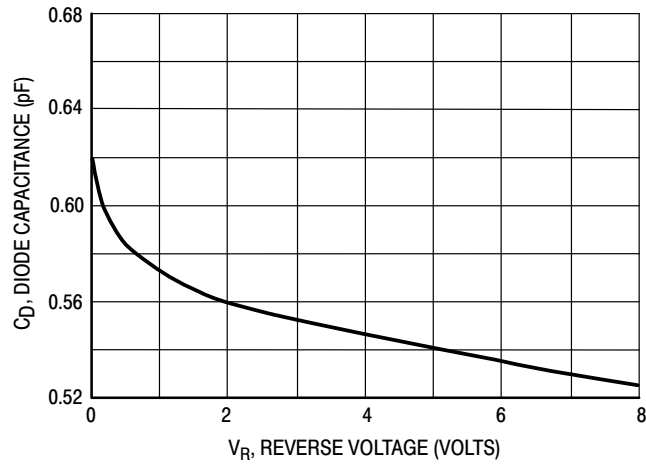
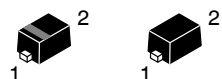


Figure 4. Capacitance

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

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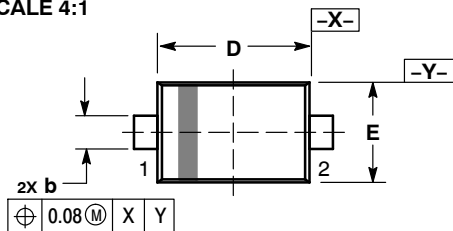


STYLE 1    STYLE 2

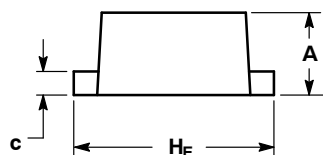
**SOD-523**  
CASE 502-01  
ISSUE E

DATE 28 SEP 2010

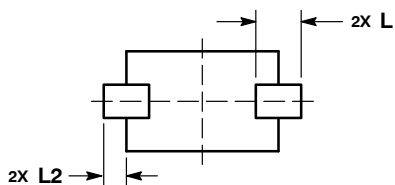
SCALE 4:1



TOP VIEW

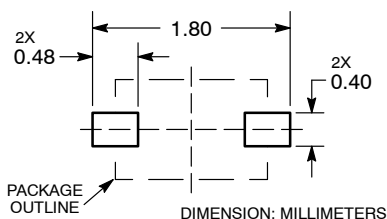


SIDE VIEW



BOTTOM VIEW

### RECOMMENDED SOLDERING FOOTPRINT\*



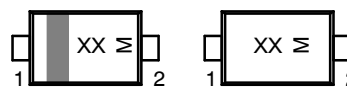
\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.50	0.60	0.70
b	0.25	0.30	0.35
c	0.07	0.14	0.20
D	1.10	1.20	1.30
E	0.70	0.80	0.90
H <sub>E</sub>	1.50	1.60	1.70
L	0.30 REF		
L2	0.15	0.20	0.25

### GENERIC MARKING DIAGRAM\*



STYLE 1

STYLE 2

XX = Specific Device Code  
M = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

STYLE 1:  
PIN 1. CATHODE (POLARITY BAND)  
2. ANODE

STYLE 2:  
NO POLARITY

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<b>DESCRIPTION:</b>	<b>SOD-523</b>	<b>PAGE 1 OF 1</b>

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